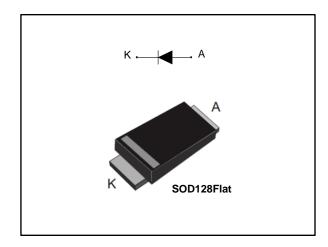


Power Schottky rectifier

Datasheet - production data



Description

This high voltage Schottky barrier rectifier device is packaged in SOD128Flat and designed for high frequency miniature switched mode power supplies and on board DC to DC converters.

Table 1: Device summary

Symbol	Value
I _{F(AV)}	3 A
V_{RRM}	60 V
T _j (max.)	175 °C
V _F (typ.)	0.49 V

Features

- Negligible switching losses
- High junction temperature capability
- Low leakage current
- Good trade-off between leakage current and forward voltage drop
- Avalanche specification
- ECOPACK® compliant component

Characteristics STPS360

1 Characteristics

Table 2: Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol	Pa	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		60	V
I _{F(AV)}	Average forward current	orward current T _L = 140 °C, δ = 0.5, square pulse		Α
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	65	А
P _{ARM}	Repetitive peak avalanche power $t_p = 10 \ \mu s, \ T_j = 125 \ ^{\circ}C$		140	W
T _{stg}	Storage temperature range		-65 to +175	°C
Tj	Operating junction temperature range ⁽¹⁾		-40 to +175	°C

Notes:

Table 3: Thermal parameters

Symbol	Parameter	Max. value	Unit
$R_{th(j-l)}$	Junction to lead	16	°C/W

Table 4: Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
. (1)	Reverse leakage current	T _j = 25 °C	V _R = 60 V	-		150	μΑ
I _R ⁽¹⁾		T _j = 125 °C		-	20	30	mΑ
	Forward voltage drop	T _j = 25 °C	I _F = 3 A	-		0.61	V
V _F ⁽²⁾		T _j = 125 °C		-	0.49	0.58	
VF		T _j = 25 °C	I _F = 6 A	-		0.80	
		T _j = 125 °C		-	0.62	0.72	

Notes:

 $^{(1)}$ Pulse test: t_p = 5 ms, δ < 2%

(2) Pulse test: t_p = 380 μs, δ < 2%

To evaluate the conduction losses use the following equation:

 $P = 0.44 \text{ x } I_{F(AV)} + 0.047 \text{ x } I_{F^2(RMS)}$

For more information, please refer to the following application notes related to the power losses.

- AN604 (Calculation of conduction losses in a power rectifier)
- AN4021 (Calculation of reverse losses in a power diode)

 $^{^{(1)}(}dP_{tot}/dT_j) < (1/R_{th(j-a)}) \ condition \ to \ avoid \ thermal \ runaway \ for \ a \ diode \ on \ its \ own \ heatsink.$

STPS360 Characteristics

1.1 Characteristics (curves)

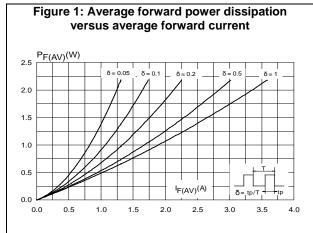


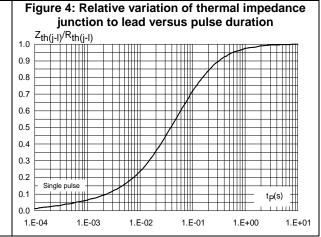
Figure 3: Normalized avalanche power derating versus pulse duration (T_j = 125 °C)

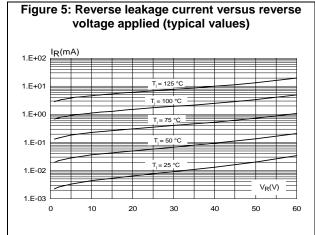
PARM(tp)
PARM(10 µs)

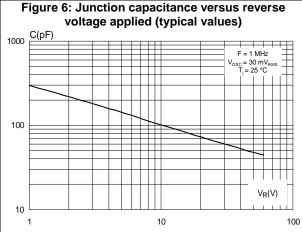
0.01

0.01

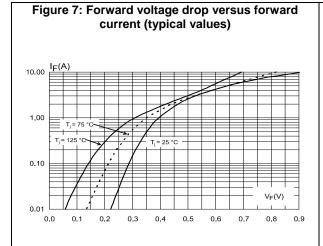
1 10 100 1000







Characteristics STPS360



versus copper surface under each lead (typical values) R_{th(j-a)}(°C/W) SOD128-Flat 150 100 Epoxy printed board FR4, e_{Cu} = 35 μm 0.5 0.0 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0

Figure 8: Thermal resistance junction to ambient

4/8 DocID029486 Rev 1

STPS360 Package information

2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

- Epoxy meets UL94, V0
- Lead-free package

2.1 SOD128Flat package information

E E1

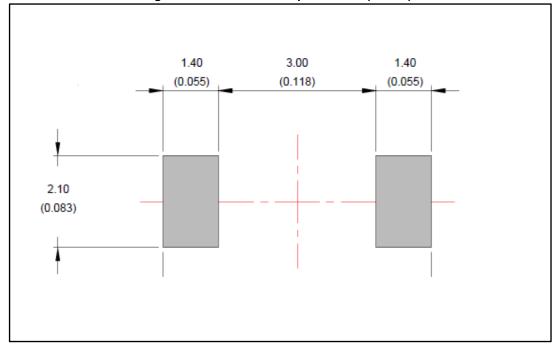
Figure 9: SOD128Flat package outline

b 2x

Table 5: SOD128Flat package mechanical data

	Dimensions				
Ref.	Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
А	0.93	1.03	0.037	0.041	
b	1.69	1.81	0.067	0.071	
С	0.10	0.22	0.004	0.009	
D	2.30	2.50	0.091	0.098	
E	4.60	4.80	0.181	0.189	
E1	3.70	3.90	0.146	0.154	
L	0.55	0.85	0.026	0.033	
L1	0.30 typ.		0.012	2 typ.	
L2	0.45 typ.		0.018 typ.		

Figure 10: SOD128Flat footprint in mm (inches)



STPS360 Ordering information

3 Ordering information

Table 6: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS360AF	360F	SOD128Flat	26.4 mg	3000	Tape and reel

4 Revision history

Table 7: Document revision history

Date	Revision	Changes
01-Jul-2016	1	Initial release.

IMPORTANT NOTICE - PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2016 STMicroelectronics - All rights reserved



单击下面可查看定价,库存,交付和生命周期等信息

>>STMicro(意法半导体)